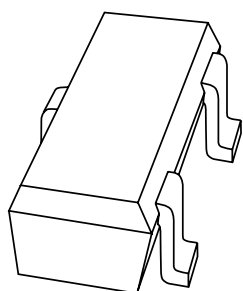


DATA SHEET



2PD601AW

NPN general purpose transistor

Preliminary specification

2002 Jun 26

NPN general purpose transistor

2PD601AW

FEATURES

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in an SC-70 (SOT323) plastic package.
PNP complement: 2PB709AW.

MARKING

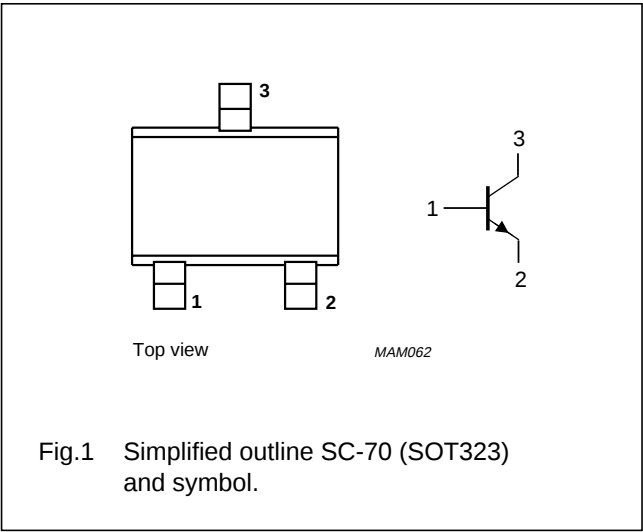
TYPE NUMBER	MARKING CODE ⁽¹⁾
2PD601AQW	*6D
2PD601ARW	*6E
2PD601ASW	*6F

Note

1. * = -: made in Hong Kong.
* = t: made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	60	V
V _{CEO}	collector-emitter voltage	open base	–	50	V
V _{EBO}	emitter-base voltage	open collector	–	6	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. For mounting conditions, see “Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18”.

NPN general purpose transistor

2PD601AW

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

- For mounting conditions, see “*Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18*”.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0$; $V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0$; $V_{CB} = 60\text{ V}$; $T_j = 150\text{ °C}$	–	5	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 100\text{ mA}$; $V_{CE} = 2\text{ V}$; note 1	90	–	
	DC current gain	$I_C = 2\text{ mA}$; $V_{CE} = 10\text{ V}$			
	2PD601AQW		160	260	
	2PD601ARW		210	340	
	2PD601ASW		290	460	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}$; $I_B = 10\text{ mA}$; note 1	–	500	mV
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$	–	3.5	pF
f_T	transition frequency	$I_C = 2\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$			
	2PD601AQW		100	–	MHz
	2PD601ARW		120	–	MHz
	2PD601ASW		140	–	MHz

Note

- Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

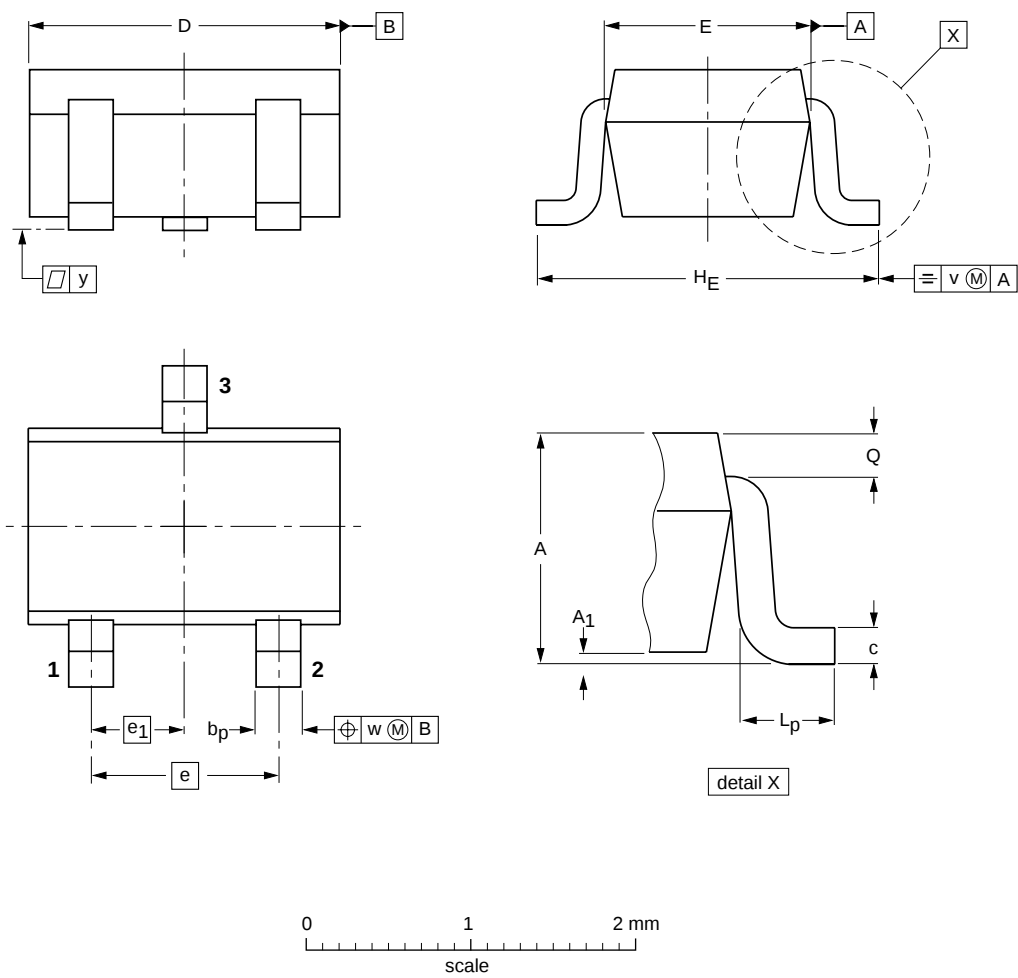
NPN general purpose transistor

2PD601AW

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN general purpose transistor

2PD601AW

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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NPN general purpose transistor

2PD601AW

NOTES

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2PD601AW

NOTES

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SCA74

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